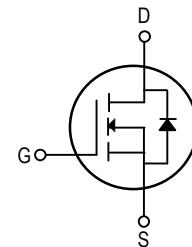


## Features

- 80V/90A
- RDS(ON)=6.5mΩ (typ.) @ VGS=10V
- Lead free and Green Device Available
- Low Rds-on to Minimize Conductive Loss
- High avalanche Current
- 100% Avalanche Tested

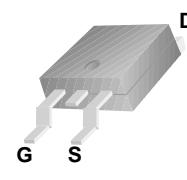


## Application

- Power Supply
- DC-DC Converters
- UPS
- Battery Management



TO-220F



TO-263

## Absolute Maximum Ratings ( $T_A=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Maximum	Unit	
$V_{DSS}$	Drain-to-Source Voltage	80	V	
$V_{GSS}$	Gate-to-Source	$\pm 25$	V	
$I_D^3$	Continuous Drain Current	$T_c=100^\circ\text{C}$	90	A
		$T_c=100^\circ\text{C}$	63	
$I_{DM}^4$	Pulsed Drain Current	360	A	
EAS <sup>5</sup>	Avalanche energy	313	mJ	
PD	Maximum Power Dissipation	$T_c=25^\circ\text{C}$	180	W
$T_J, T_{STG}$	Junction & Storage Temperature Range		-55~175	°C

## Thermal Characteristics

Symbol	Parameter	Typical	Unit
$R\theta_{jc}$	Thermal Resistance-Junction to Case	0.63	°C/W
$R\theta_{ja}$	Thermal Resistance-Junction to Ambient	62.5	

## Electrical Characteristics (TA=25°C unless otherwise noted)

Symbol	Parameter	Test Conditions	Min.	Typ	Max.	Unit
<b>Static Characteristics</b>						
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =250uA	80	—	—	V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> =80V, V <sub>GS</sub> =0V	—	—	1	uA
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250uA	2	3	4	V
I <sub>GSS</sub>	Gate Leakage Current	V <sub>GS</sub> =±25V, V <sub>DS</sub> =0V	—	—	±100	nA
R <sub>DS(on)</sub> <sup>1</sup>	Drain-Source On-Resistance	V <sub>GS</sub> =10V, I <sub>D</sub> =40A	—	6.5	8.5	mΩ
			—	—	—	
<b>Diode Characteristics</b>						
V <sub>SD</sub> <sup>1</sup>	Diode Forward Voltage	I <sub>SD</sub> =50A, V <sub>GS</sub> =0V	—	0.9	1.3	V
I <sub>S</sub> <sup>3</sup>	Diode Continuous Forward Current		—	—	97	A
t <sub>rr</sub>	Reverse Recovery Time	I <sub>S</sub> =50A,	—	45	—	nS
Q <sub>rr</sub>	Reverse Recovery Charge	dI/dt=100A/us	—	65	—	nC
<b>Dynamic Characteristics</b> <sup>2</sup>						
C <sub>iss</sub>	Input Capacitance	V <sub>GS</sub> =0V, V <sub>DS</sub> =50V Frequency=1MHz	—	3175	—	pF
C <sub>oss</sub>	Output Capacitance		—	440	—	
C <sub>rss</sub>	Reverse Transfer Capacitance		—	268	—	
t <sub>d(on)</sub>	Turn-On Delay Time	V <sub>DS</sub> =40V, I <sub>D</sub> =50A, V <sub>GS</sub> =10V,(Note1,4)	—	49	—	nS
t <sub>r</sub>	Rise Time		—	64	—	
t <sub>d(off)</sub>	Turn-Off Delay Time		—	139	—	
t <sub>f</sub>	Fall Time		—	48	—	
<b>Gate Charge Characteristics</b> <sup>2</sup>						
Q <sub>g</sub>	Total Gate Charge	V <sub>DS</sub> =64V, I <sub>D</sub> =50A, V <sub>GS</sub> =10V,(Note1,4)	—	76	—	nC
Q <sub>gs</sub>	Gate-to-Source Charge		—	21	—	
Q <sub>gd</sub>	Gate-to-Drain Charge		—	24	—	

Note: 1: Pulse test; pulse width  $\leq$  300us, duty cycle  $\leq$  2%.

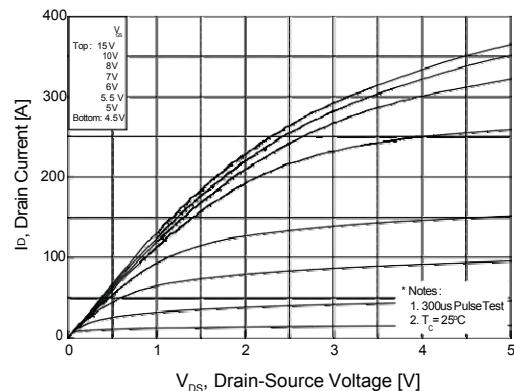
2: Guaranteed by design, not subject to production testing.

3: Package limitation current is 100A.Calculated continuous current based on maximum allowable junction temperature.

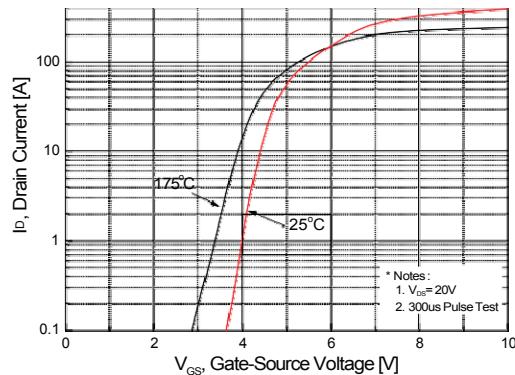
4: Repetitive rating, pulse width limited by max junction temperature.

5: Starting TJ = 25°C,L = 1mH,IAS = 25A.

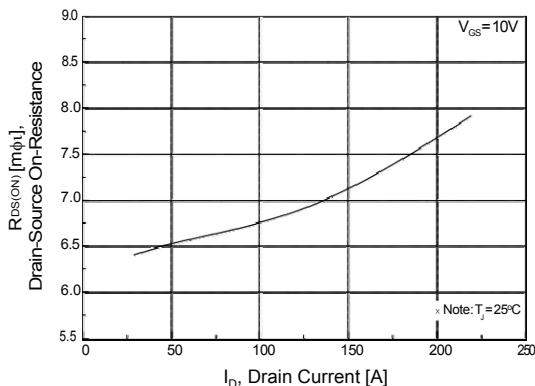
### Typical Characteristics



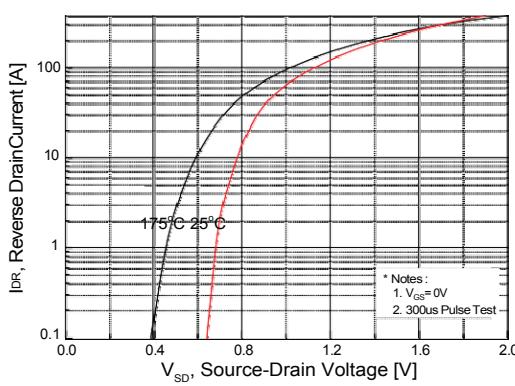
**Figure 1. On Region Characteristics**



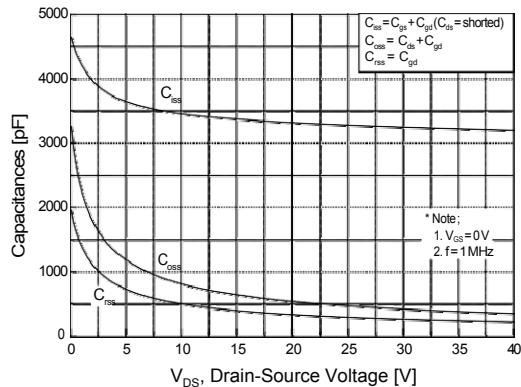
**Figure 2. Transfer Characteristics**



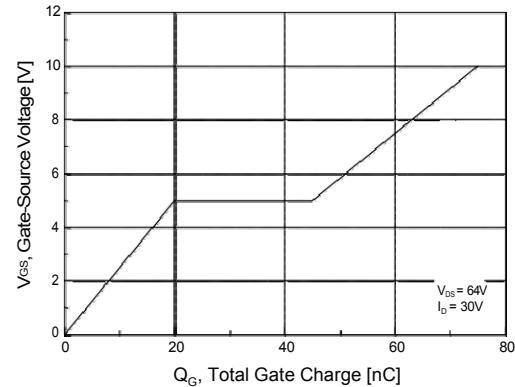
**Figure 3. On Resistance Variation vs. Drain Current and Gate Voltage**



**Figure 4. Body Diode Forward Voltage Variation with Source Current and Temperature**

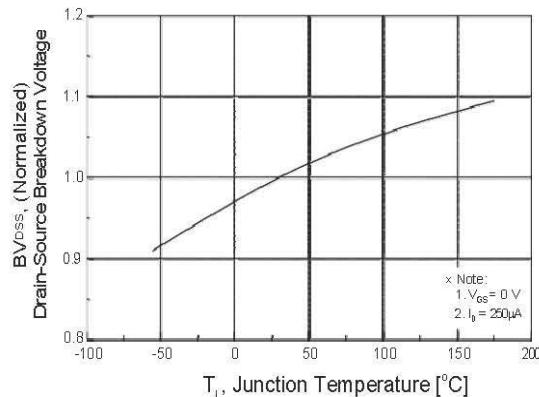


**Figure 5. Capacitance Characteristics**

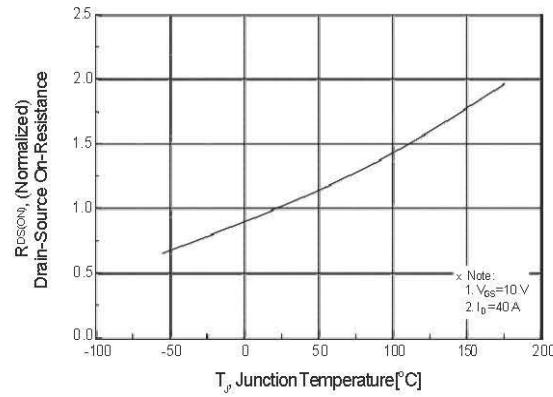


**Figure 6. Gate Charge Characteristics**

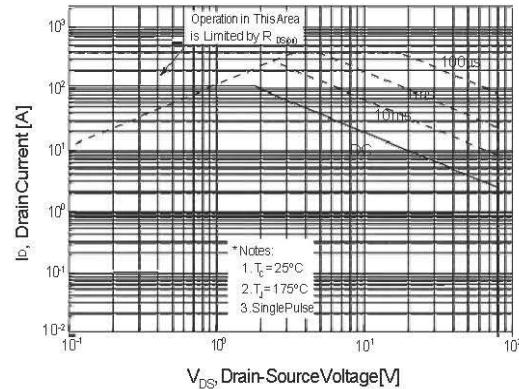
**Typical Characteristics (continued)**



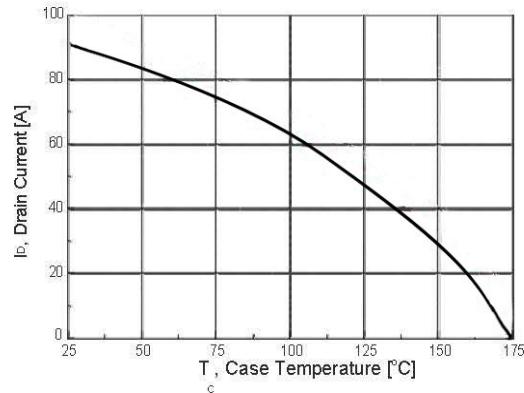
**Figure 7. Breakdown Voltage Variation  
vs Temperature**



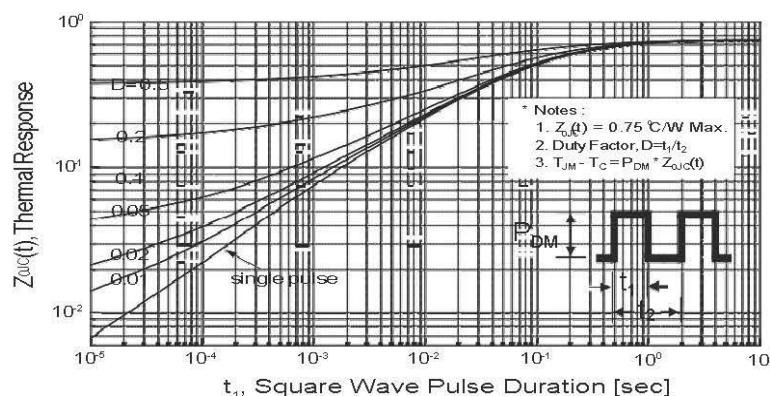
**Figure 8. On-Resistance Variation  
vs Temperature**



**Figure 9. Maximum Safe Operating Area**



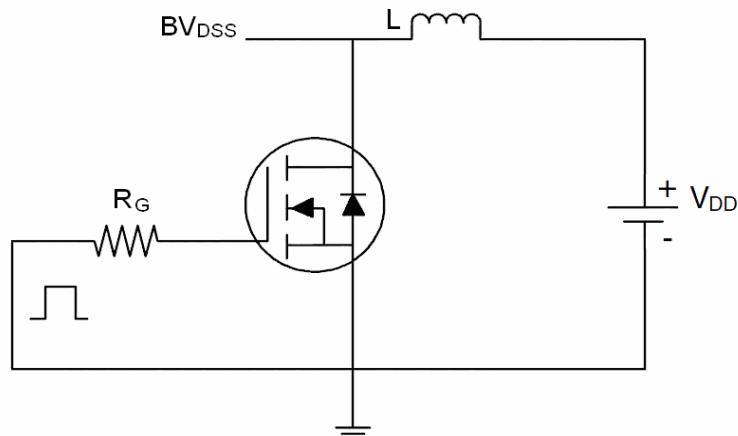
**Figure 10. Maximum Drain Current  
vs Case Temperature**



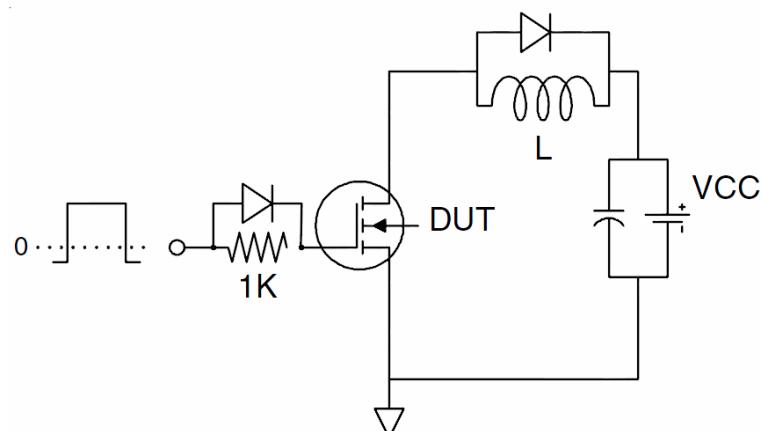
**Figure 11. Transient Thermal Response Curve**

### Test Circuit

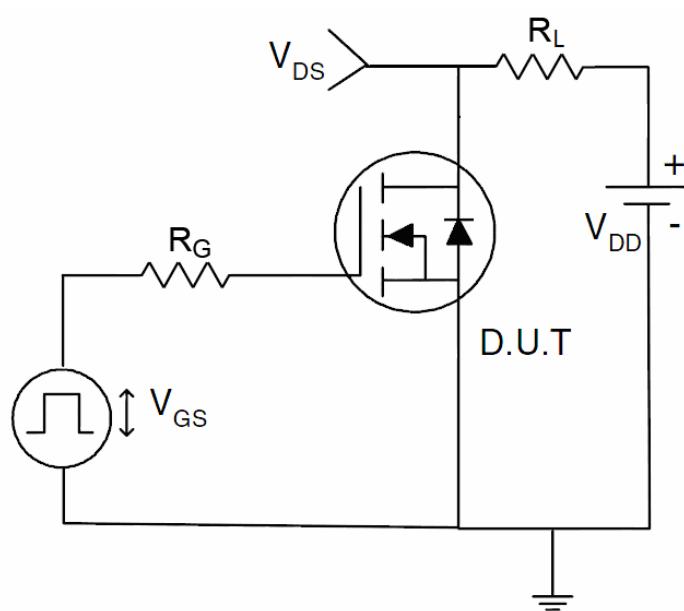
#### 1) E<sub>AS</sub> test Circuit



#### 2) Gate charge test Circuit



#### 3) Switch Time Test Circuit



# X-ON Electronics

Largest Supplier of Electrical and Electronic Components

***Click to view similar products for MOSFET category:***

***Click to view products by PUOLOP manufacturer:***

Other Similar products are found below :

[614233C](#) [648584F](#) [NTNS3A92PZT5G](#) [IRFD120](#) [IRFF430](#) [JANTX2N5237](#) [2N7000](#) [2SK2464-TL-E](#) [FCA20N60\\_F109](#) [FDZ595PZ](#) [AOD464](#)  
[2SK2267\(Q\)](#) [2SK2545\(Q,T\)](#) [405094E](#) [423220D](#) [MIC4420CM-TR](#) [VN1206L](#) [614234A](#) [715780A](#) [SSM6J414TU,LF\(T](#) [751625C](#)  
[IPP60R600P6XKSA1](#) [RJK60S5DPK-M0#T0](#) [BSC884N03MS G](#) [BSF024N03LT3 G](#) [PSMN4R2-30MLD](#) [TK31J60W5,S1VQ\(O](#)  
[2SK2614\(TE16L1,Q\)](#) [DMN1017UCP3-7](#) [EFC2J004NUZTDG](#) [FCAB21350L1](#) [P85W28HP2F-7071](#) [DMN1053UCP4-7](#) [NTE2384](#) [NTE2969](#)  
[NTE6400A](#) [DMN2080UCB4-7](#) [DMN61D9UWQ-13](#) [US6M2GTR](#) [DMN31D5UDJ-7](#) [SSM6P54TU,LF](#) [DMP22D4UFO-7B](#)  
[IPS60R3K4CEAKMA1](#) [DMN1006UCA6-7](#) [DMN16M9UCA6-7](#) [STF5N65M6](#) [STU5N65M6](#) [C3M0021120D](#) [DMN13M9UCA6-7](#)  
[BSS340NWH6327XTSA1](#)